

“Elucidating the effects of gas flow rate on an SF₆ inductively coupled plasma and on the silicon etch rate, by a combined experimental and theoretical investigation”. Tinck S, Tillocher T, Dussart R, Neyts EC, Bogaerts A, Journal of physics: D: applied physics **49**, 385201 (2016). <http://doi.org/10.1088/0022-3727/49/38/385201>